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W29N02GV
2G-BIT 3.3V
NAND FLASH MEMORY

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1. GENERAL DESCRIPTION

The W29N02GV (2G-bit) NAND Flash memory provides a storage solution for embedded systems with limited space, pins and power. It is ideal for code shadowing to RAM, solid state applications and storing media data such as, voice, video, text and photos. The device operates on a single 2.7V to 3.6V power supply with active current consumption as low as 25mA at 3V and 10uA for CMOS standby current.

The memory array totals 276,824,064bytes, and organized into 2,048 erasable blocks of 135,168 bytes. Each block consists of 64 programmable pages of 2,112-bytes each. Each page consists of 2,048-bytes for the main data storage area and 64-bytes for the spare data area (The spare area is typically used for error management functions).

The W29N02GV supports the standard NAND flash memory interface using the multiplexed 8-bit bus to transfer data, addresses, and command instructions. The five control signals, CLE, ALE, #CE, #RE and #WE handle the bus interface protocol. Also, the device has two other signal pins, the #WP (Write Protect) and the RY/#BY (Ready/Busy) for monitoring the device status.

2. FEATURES

- **Basic Features**
  - Density : 2Gbit (Single chip solution)
  - Vcc : 2.7V to 3.6V
  - Bus width : x8
  - Operating temperature
    - Industrial: -40°C to 85°C
- **Single-Level Cell (SLC) technology.**
- **Organization**
  - Density: 2G-bit/256M-byte
  - Page size
    - 2,112 bytes (2048 + 64 bytes)
  - Block size
    - 64 pages (128K + 4K bytes)
- **Highest Performance**
  - Read performance (Max.)
    - Random read: 25us
    - Sequential read cycle: 25ns
  - Write Erase performance
    - Page program time: 250us(typ.)
    - Block erase time: 2ms(typ.)
  - Endurance 100,000 Erase/Program Cycles(1)
  - 10-years data retention
- **Command set**
  - Standard NAND command set
  - Additional command support
    - Sequential Cache Read
    - Random Cache Read
    - Cache Program
    - Copy Back
    - Two-plane operation
  - Contact Winbond for OTP feature
  - Contact Winbond for block Lock feature
- **Lowest power consumption**
  - Read: 25mA(typ.)
  - Program/Erase: 25mA(typ.)
  - CMOS standby: 10uA(typ.)
- **Space Efficient Packaging**
  - 48-pin standard TSOP1
  - 63-ball VFBGA
  - Contact Winbond for stacked packages/KGD

Note:

1. **Endurance specification is based on 1bit/528 byte ECC (Error Correcting Code).**

3. PACKAGE TYPES AND PIN CONFIGURATIONS

W29N02GV is offered in a 48-pin TSOP1 package (Code S) and 63-ball VFBGA package (Code B) as shown in Figure 3-1 to 3-3, respectively. Package diagrams and dimensions are illustrated in Section: Package Dimensions.

3.1 Pin assignment 48-pin TSOP1(x8)

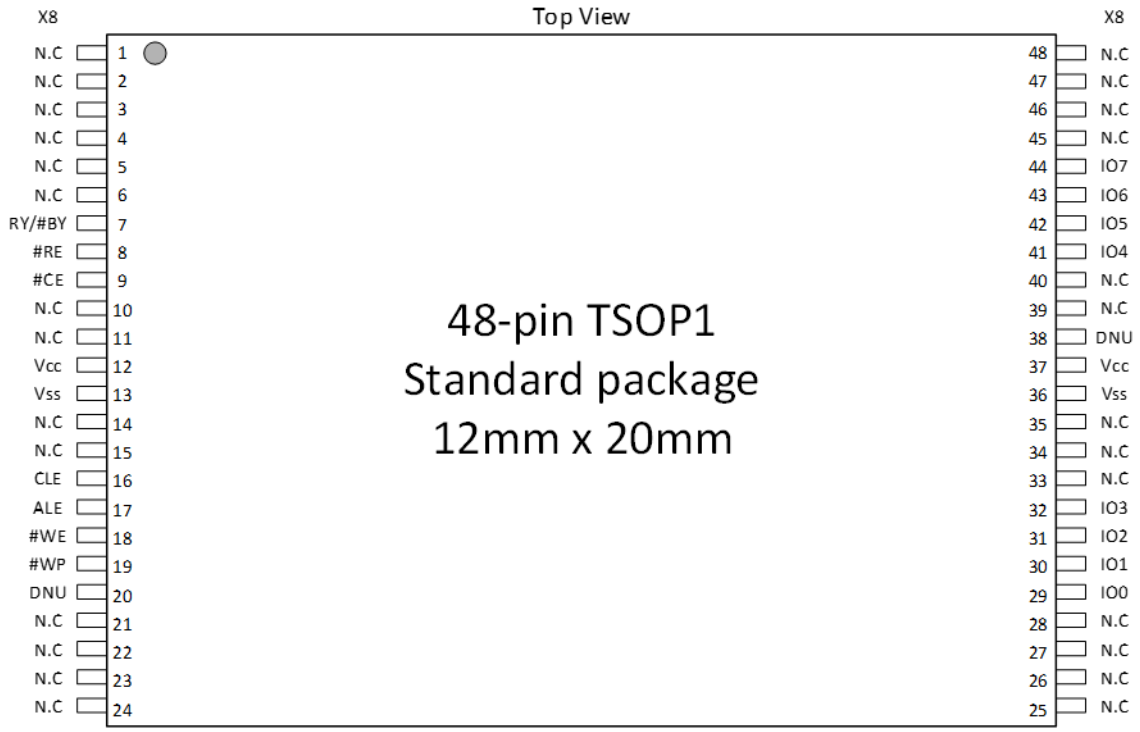

Figure 3-1 Pin Assignment 48-pin TSOP1 (Package code S)

3.2 Pin assignment 63 ball VFBGA (x8)

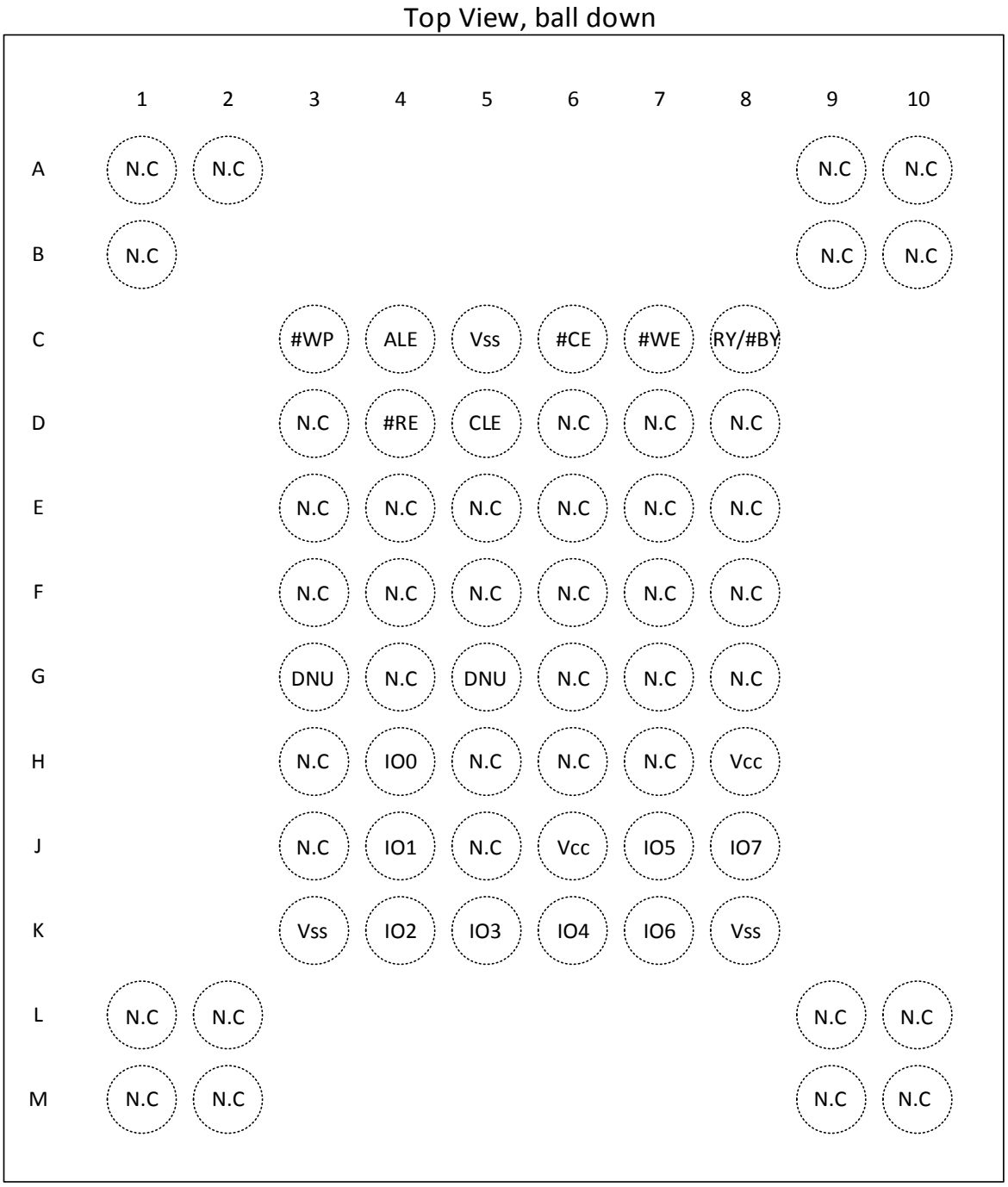

Figure 3-2 Pin Assignment 63-ball VFBGA (Package code B)

3.3 Pin Descriptions

PIN NAME	I/O	FUNCTION
#WP	I	Write Protect
ALE	I	Address Latch Enable
#CE	I	Chip Enable
#WE	I	Write Enable
RY/#BY	O	Ready/Busy
#RE	I	Read Enable
CLE	I	Command Latch Enable
I/O[0-7]	I/O	Data Input/Output (x8)
Vcc	Supply	Power supply
Vss	Supply	Ground
DNU	-	Do Not Use: DNUs must be left unconnected.
N.C	-	No Connect

Table 3-1 Pin Descriptions

Note:

1. **Connect all Vcc and Vss pins to power supply or ground. Do not leave Vcc or Vss disconnected.**

4. PIN DESCRITPIONS

4.1 Chip Enable (#CE)

#CE pin enables and disables device operation. When #CE is high the device is disabled and the I/O pins are set to high impedance and enters into standby mode if not busy. When #CE is set low the device will be enabled, power consumption will increase to active levels and the device is ready for Read and Write operations.

4.2 Write Enable (#WE)

#WE pin enables the device to control write operations to input pins of the device. Such as, command instructions, addresses and data that are latched on the rising edge of #WE.

4.3 Read Enable (#RE)

#RE pin controls serial data output from the pre-loaded Data Register. Valid data is present on the I/O bus after the tREA period from the falling edge of #RE. Column addresses are incremented for each #RE pulse.

4.4 Address Latch Enable (ALE)

ALE pin controls address input to the address register of the device. When ALE is active high, addresses are latched via the I/O pins on the rising edge of #WE.

4.5 Command Latch Enable (CLE)

CLE pin controls command input to the command register of the device. When CLE is active high, commands are latched into the command register via I/O pins on the rising edge of #WE.

4.6 Write Protect (#WP)

#WP pin can be used to prevent the inadvertent program/erase to the device. When #WP pin is active low, all program/erase operations are disabled.

4.7 Ready/Busy (RY/#BY)

RY/#BY pin indicates the device status. When RY/#BY output is low, it indicates that the device is processing either a program, erase or read operations. When it returns to high, those operations have completed. RY/#BY pin is an open drain.

4.8 Input and Output (I/Ox)

I/Ox bi-directional pins are used for the following; command, address and data operations.

5. BLOCK DIAGRAM

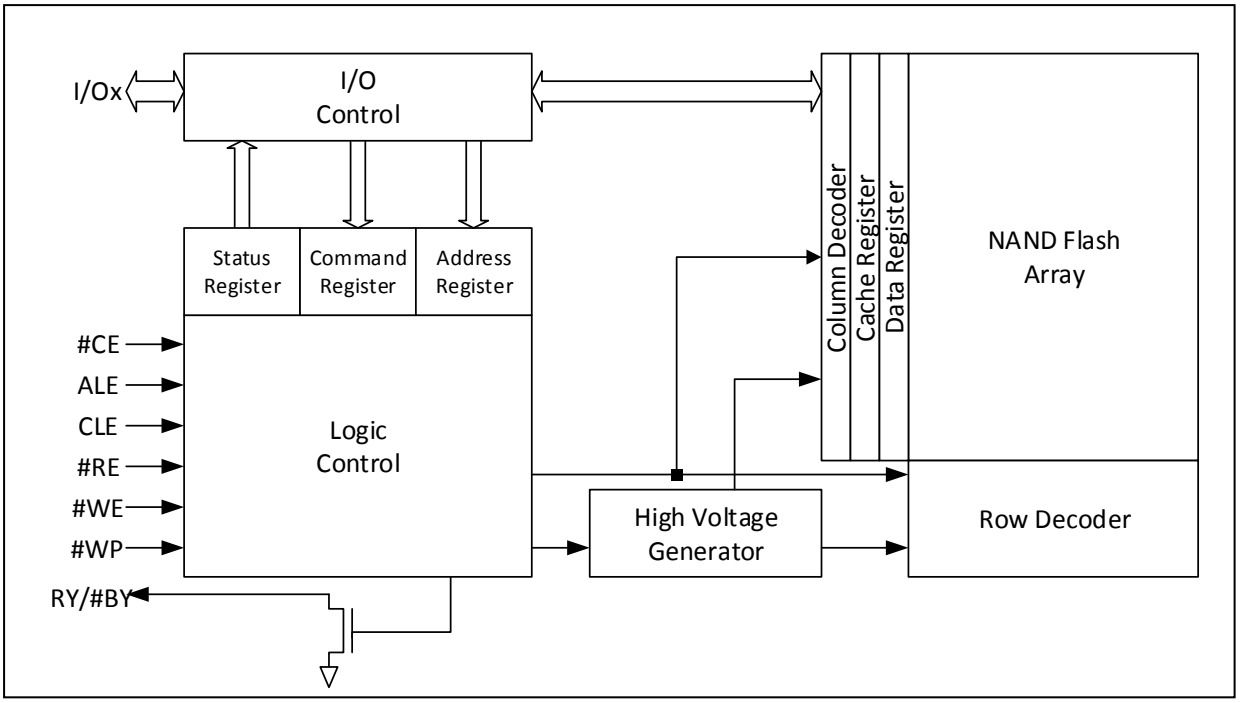

Figure 5-1 NAND Flash Memory Block Diagram

6. MEMORY ARRAY ORGANIZATION

6.1 Array Organization (x8)

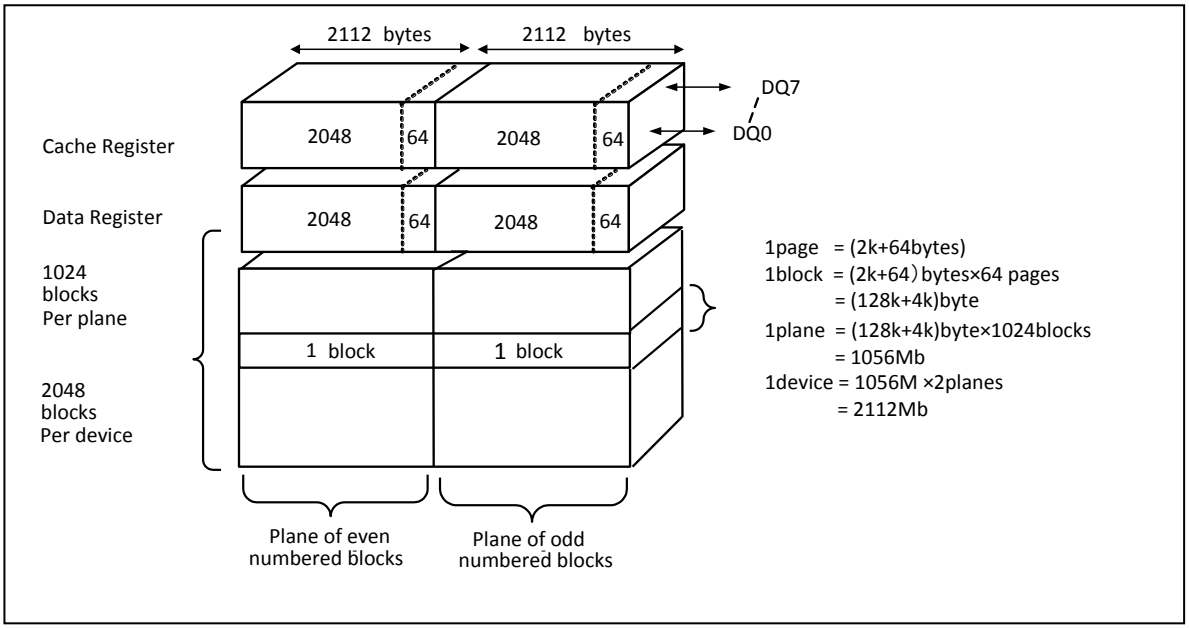

Figure 6-1 Array Organization

	I/O7	I/O6	I/O5	I/O4	I/O3	I/O2	I/O1	I/O0
1st cycle	A7	A6	A5	A4	A3	A2	A1	A0
2nd cycle	L	L	L	L	A11	A10	A9	A8
3rd cycle	A19	A18	A17	A16	A15	A14	A13	A12
4th cycle	A27	A26	A25	A24	A23	A22	A21	A20
5th cycle	L	L	L	L	L	L	L	A28

Table 6-1 Addressing

Notes:

1. **"L" indicates a low condition, which must be held during the address cycle to insure correct processing.**
2. **A0 to A11 during the 1st and 2nd cycles are column addresses. A12 to A28 during the 3rd, 4th and 5th cycles are row addresses.**
3. **A18 is plane address**
4. **The device ignores any additional address inputs that exceed the device's requirement.**

7. MODE SELECTION TABLE

MODE		CLE	ALE	#CE	#WE	#RE	#WP
Read mode	Command input	H	L	L		H	X
	Address input	L	H	L		H	X
Program Erase mode	Command input	H	L	L		H	H
	Address input	L	H	L		H	H
Data input		L	L	L		H	H
Sequential Read and Data output		L	L	L	H		X
During read (busy)		X	X	X	X	H	X
During program (busy)		X	X	X	X	X	H
During erase (busy)		X	X	X	X	X	H
Write protect		X	X	X	X	X	L
Standby		X	X	H	X	X	0V/Vcc

Table 7-1 Mode Selection

Notes:

1. **"H" indicates a HIGH input level, "L" indicates a LOW input level, and "X" indicates a Don't Care Level.**
2. **#WP should be biased to CMOS HIGH or LOW for standby.**

8. COMMAND TABLE

COMMAND	1ST CYCLE	2ND CYCLE	3rd CYCLE	4th CYCLE	Acceptable during busy
PAGE READ	00h	30h			
READ for COPY BACK	00h	35h			
SEQUENTIAL CACHE READ	31h				
RANDOM CACHE READ	00h	31h			
LAST ADDRESS CACHE READ	3Fh				
READ ID	90h				
READ STATUS	70h				Yes
RESET	FFh				Yes
PAGE PROGRAM	80h	10h			
PROGRAM for COPY BACK	85h	10h			
CACHE PROGRAM	80h	15h			
BLOCK ERASE	60h	D0h			
RANDOM DATA INPUT*1	85h				
RANDOM DATA OUTPUT*1	05h	E0h			
READ PARAMETER PAGE	ECh				
READ UNIQUE ID	EDh				
GET FEATURES	EEh				
SET FEATURES	EFh				
READ STATUS ENHANCED	78h				Yes
TWO PLANE READ PAGE	00h	00h	30h		
TWO PLANE READ FOR COPY BACK	00h	00h	35h		
TWO PLANE RANDOM DATA READ	06h	E0h			
TWO PLANE PROGRAM(TRADITIONAL)	80h	11h	81h	10h	
TWO PLANE PROGRAM(ONFI)	80h	11h	80h	10h	
TWO PLANE CACHE PROGRAM(START/CONTINUE)(TRADITIONAL)	80h	11h	81h	15h	
TWO PLANE CACHE PROGRAM(START/CONTINUE) (ONFI)	80h	11h	80h	15h	
TWO PLANE CACHE PROGRAM(END)(TRADITIONAL)	80h	11h	81h	10h	
TWO PLANE CACHE PROGRAM(END)(ONFI)	80h	11h	80h	10h	
TWO PLANE PROGRAM FOR COPY BACK(TRADITIONAL)	85h	11h	81h	10h	
TWO PLANE PROGRAM FOR COPY BACK(ONFI)	85h	11h	85h	10h	

TWO PLANE BLOCK ERASE(TRADITIONAL)	60h	60h	D0h		
TWO PLANE BLOCK ERASE(ONFI)	60h	D1h	60h	D0h	

Table 8-1 Command Table

Notes:

1. **RANDOM DATA INPUT and RANDOM DATA OUTPUT command is only to be used within a page.**
2. **Any commands that are not in the above table are considered as undefined and are prohibited as inputs.**
3. **Do not cross plane address boundaries when using Copy Back Read and Program for copy back.**

9. DEVICE OPERATIONS

9.1 READ operation

9.1.1 PAGE READ (00h-30h)

When the device powers on, 00h command is latched to command register. Therefore, system only issues five address cycles and 30h command for initial read from the device. This operation can also be entered by writing 00h command to the command register, and then write five address cycles, followed by writing 30h command. After writing 30h command, the data is transferred from NAND array to Data Register during tR. Data transfer progress can be done by monitoring the status of the RY/#BY signal output. RY/#BY signal will be LOW during data transfer. Also, there is an alternate method by using the READ STATUS (70h) command. If the READ STATUS command is issued during read operation, the Read (00h) command must be re-issued to read out the data from Data Register. When the data transfer is complete, RY/#BY signal goes HIGH, and the data can be read from Data Register by toggling #RE. Read is sequential from initial column address to the end of the page. (See Figure 9-1)

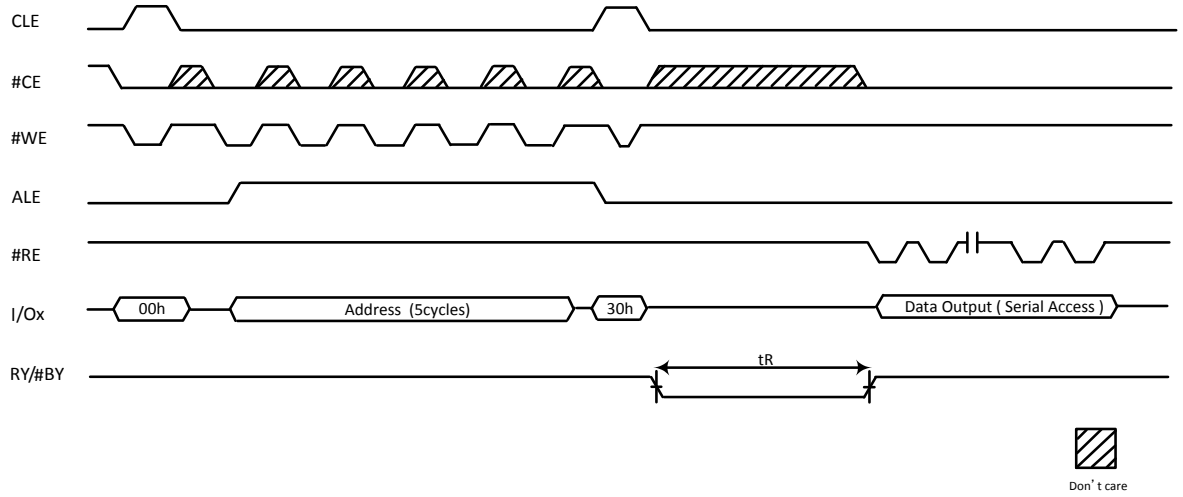

Figure 9-1 Page Read Operations

9.1.2 CACHE READ OPERATIONS

To obtain a higher degree of performance read operations, the device's Cache and Data Register can be used independent of each other. Data can be read out from the Cache Register, while array data is transferred from the NAND Array to the Data Register.

The CACHE READ mode starts with issuing a PAGE READ command (00h-30h) to transfer a page of data from NAND array to the Cache Register. RY/#BY signal will go LOW during data transfer indicating a busy status. Copying the next page of data from the NAND array to the Data Register while making the Cache Register page data available is done by issuing either a SEQUENTIAL CACHE READ (31h) or RANDOM CACHE READ (00h-31h) command. The SEQUENTIAL CACHE READ mode will copy the next page of data in sequence from the NAND array to the Data Register or use the RANDOM CACHE READ mode (00h-31h) to copy a random page of data from NAND array to the Data Register. The RY/#BY signal goes LOW for a period of tRCBSY during the page data transfer from NAND array to the Data Register. When RY/#BY goes HIGH, this means that the

Cache Register data is available and can be read out of the Cache Register by with toggling #RE, which starts at address column 0. If it is desired to start at a different column address, a RANDOM DATA OUTPUT (05h-E0h) command can be used to change the column address to read out the data.

At this point in the procedure when completing the read of the desired number of bytes, one of two things can be chosen. Continue CACHE READ (31h or 00h-31h) operations or end the CACHE READ mode with a LAST ADDRESS CACHE READ (3Fh) command.

To continue with the read operations, execute the CACHE READ (31h or 00h-31h) command. The RY/#BY signal goes LOW for the period of tRCBSY while data is copied from Data Register to the Cache Register and the next page of data starts being copied from the NAND array to the Data Register. When RY/#BY signal goes HIGH signifying that the Cache Register data is available, at this time #RE can start toggling to output the desired data starting at column 0 address or using the RANDOM DATA OUPUT command for random column address access.

To terminate the CACHE READ operations a LAST ADDRESS CACHE READ (3Fh) command is issued, RY/#BY signal goes LOW and the Data Register contents is copied to the Cache Register. At the completion of the Data Register to Cache Register transfer, RY/#BY goes HIGH indicating data is available at the output of the Cache Register. At this point Data can be read by toggling #RE starting at column address 0 or using the RANDOM DATA OUPUT command for random column address access. The device NAND array is ready for next command set.

9.1.2.1. SEQUENTIAL CACHE READ (31h)

The SEQUENTIAL CACHE READ (31h) copies the next page of data in sequence within block to the Data Register while the previous page of data in the Cache Register is available for output. This is done by issuing the command (31h), RY/#BY signal goes LOW and the STATUS REGISTER bits 6 and 5 = “00” for the period of tRCBSY. When RY/#BY signal goes HIGH and STATUS REGISTER bits 6 and 5 = “10”, data at the Cache Register is available. The data can be read out from the Cache Register by toggling #RE, starting address is column 0 or by using the RANDOM DATA OUTPUT command for random column address access.

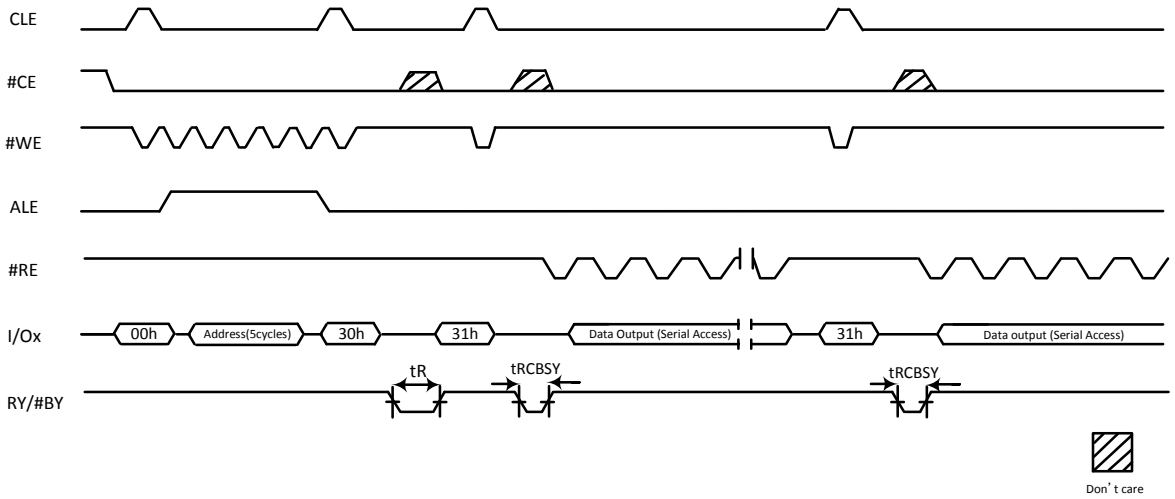

Figure 9-2 Sequential Cache Read Operations

9.1.2.2. RANDOM CACHE READ (00h-31h)

The RANDOM CACHE READ (00h-31h) will copy a particular page from NAND array to the Data Register while the previous page of data is available at the Cache Register output. Perform this function by first issuing the 00h command to the Command Register, then writing the five address cycles for the desired page of data to the Address Register. Then write the 31h command to the Command Register. Note; the column address bits are ignored.

After the RANDOM CACHE READ command is issued, RY/#BY signal goes LOW and STATUS REGISTER bits 6 and 5 equal “00” for the period of tRCBSY. When RY/#BY signal goes HIGH and STATUS REGISTER bits 6 and 5 equal “10”, the page data in the Cache Register is available. The data can read out from the Cache Register by toggling #RE, the starting column address will be 0 or use the RANDOM DATA OUTPUT (05h-E0h) command change the column address to start reading out the data.

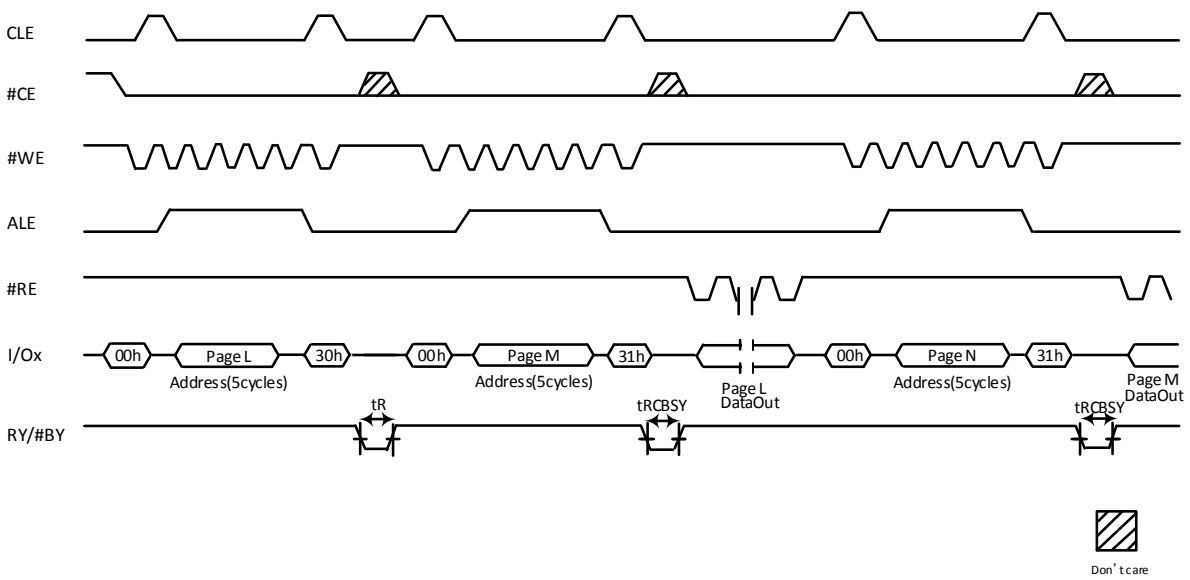

Figure 9-3 Random Cache Read Operation

9.1.2.3. LAST ADDRESS CACHE READ (3Fh)

The LAST ADDRESS CACHE READ (3Fh) copies a page of data from the Data Register to the Cache Register without starting the another cache read. After writing the 3Fh command, RY/#BY signal goes LOW and STATUS REGISTER bits 6 and 5 equals “00” for the period of tRCBSY. When RY/#BY signal goes HIGH and STATUS REGISTER bits 6 and 5 equals “11”, the Cache Register data is available, and the device NAND array is in ready state. The data can read out from the Cache Register by toggling #RE, starting at address column 0 or us RANDOM DATA OUTPUT (05h-E0h) command to change the column address to read out the data.

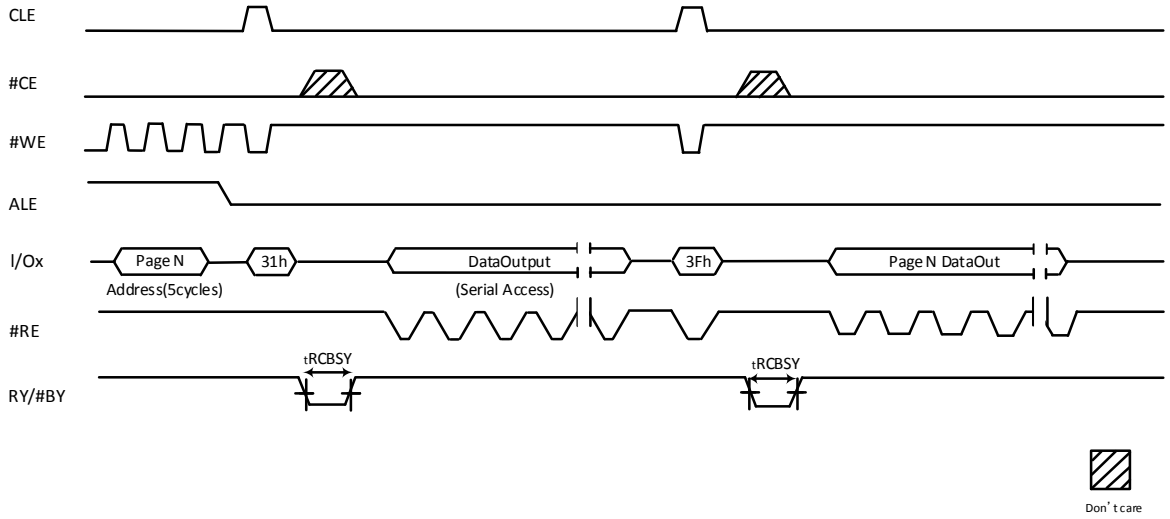

Figure 9-4 Last Address Cache Read Operation

9.1.3 TWO PLANE READ (00h-00h-30h)

TWO PLANE READ (00h-00h-30h) transfers two pages data from the NAND array to the data registers. Each page address have to be indicated different plane address.

To set the TWO PLANE READ mode, write the 00h command to the command register, and then write five address cycles for plane 0. Secondly, write the 00h command to the command register, and five address cycles for plane 1. Finally, the 30h command is issued. The first-plane and second-plane addresses must be identical for all of issued address except plane address.

After the 30h command is written, page data is transferred from both planes to their respective data registers in tR. RY/#BY goes LOW While these are transfered,. When the transfers are complete, RY/#BY goes HIGH. To read out the data, at first, system writes TWO PLANE RAMDOM DATA READ (06h-E0h) command to select a plane, next, repeatedly pulse #RE to read out the data from selected plane. To change the plane address, issues TWO PLANE RANDOM DATA READ (06h-E0h) command to select the another plane address, then repeatedly pulse #RE to read out the data from the selected plane data register.

Alternatively, data transfers can be monitored by the READ STATUS (70h). When the transfers are complete, status register bit 6 is set to 1. To read data from the first of the two planes even when

READ STATUS ENHANCED (78h) command is used, the system must issue the TWO PLANE RANDOM DATA READ (06h-E0h) command at first and pulse #RE repeatedly.

Write a TWO PLANE RANDOM DATA READ (06h-E0h) command to select the other plane ,after the data cycle is complete. pulse #RE repeatedly to output the data beginning at the specified column address,

During TWO PLANE READ operation,the READ STATUS ENHANCED (78h) command is prohibited .

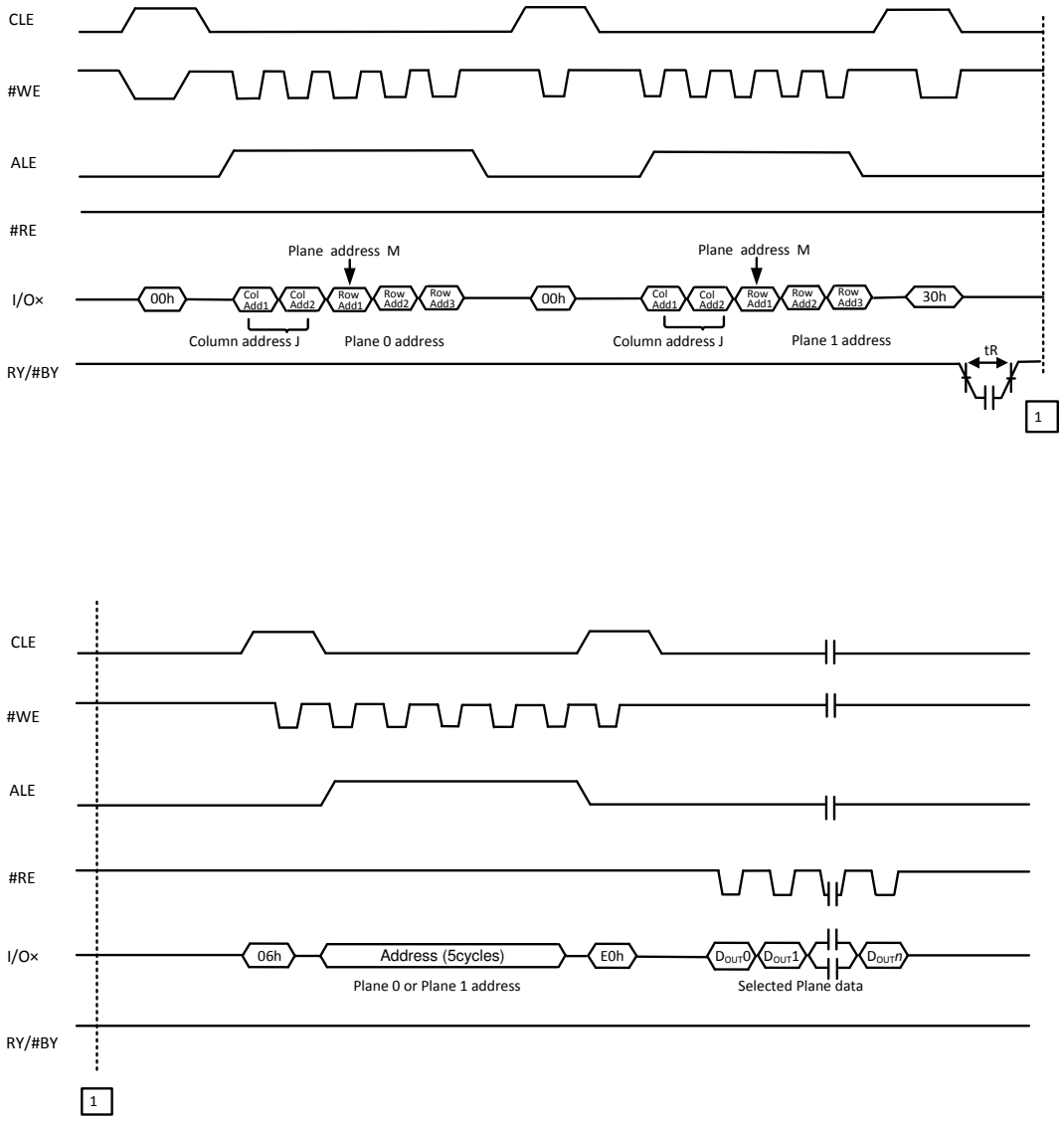

Figure 9-5 Two Plane Read Page (00h-00h-30h) Operation

9.1.4 RANDOM DATA OUTPUT (05h-E0h)

The RANDOM DATA OUTPUT allows the selection of random column addresses to read out data from a single or multiple of addresses. The use of the RANDOM DATA OUTPUT command is available after the PAGE READ (00h-30h) sequence by writing the 05h command following by the two cycle column address and then the E0h command. Toggling #RE will output data sequentially. The RANDOM DATA OUTPUT command can be issued multiple times, but limited to the current loaded page.

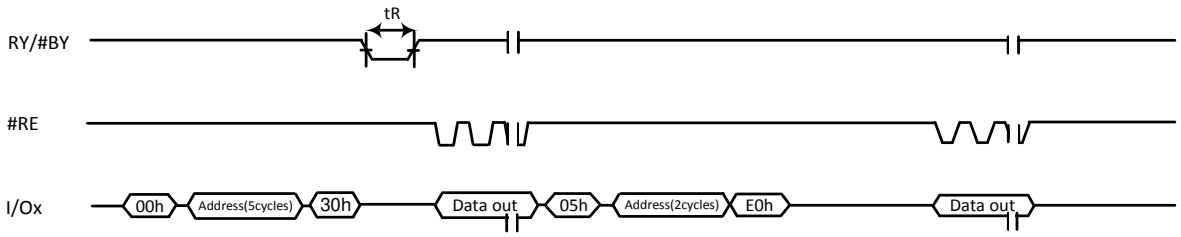

Figure 9-6 Random Data Output

9.1.4.1. TWO PLANE RANDOM DATA OUTPUT (06h-E0h)

TWO PLANE RANDOM DATA READ (06h-E0h) command can indicate to specified plane and column address on cache register . This command is accepted by a device when it is ready.

Issuing 06h to the command register, two column address cycles, three row address cycles, E0h are followed, this enables data output mode on the address device's cache register at the specified column address. After the E0h command , the host have to wait at least tWHR before requesting data output. The selected device is in data output mode until another valid command is issued.

The TWO PLANE RANDOM DATA READ (06h-E0h) command is used to select the cache register to be enabled for data output. When the data output is complete on the selected plane, the command can be issued again to start data output on another plane.

If there is a need to update the column address without selecting a new cache register, the RANDOM DATA READ (05h-E0h) command can be used instead.

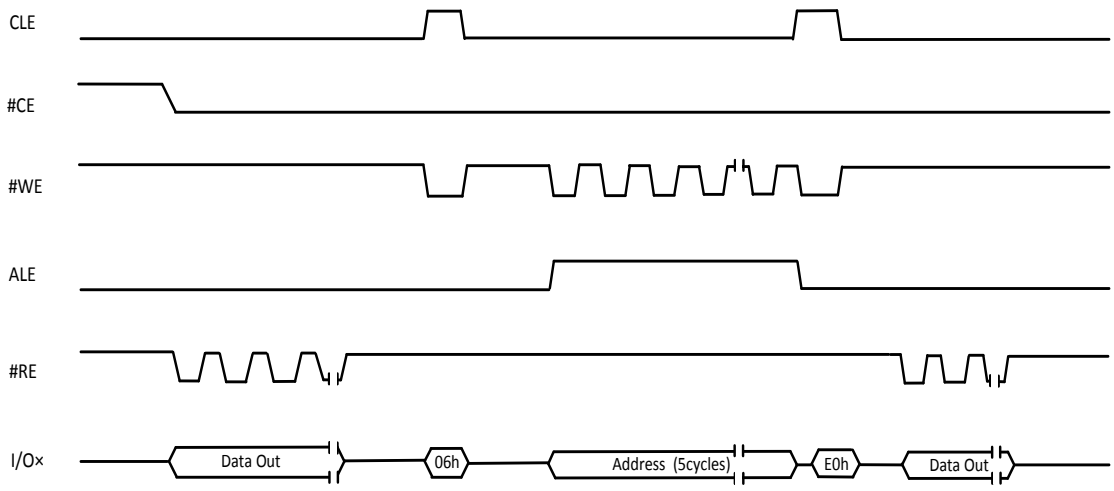

Figure 9-7 Two Plane Random Data Read (06h-E0h) Operation

9.1.5 READ ID (90h)

READ ID command is comprised of two modes determined by the input address, device (00h) or ONFI (20h) identification information. To enter the READ ID mode, write 90h to the Command Register followed by a 00h address cycle, then toggle #RE for 5 single byte cycles, W29N02GV. The pre-programmed code includes the Manufacturer ID, Device ID, and Product-Specific Information (see Table 9.1). If the READ ID command is followed by 20h address, the output code includes 4 single byte cycles of ONFI identifying information (See Table 9.2). The device remains in the READ ID Mode until the next valid command is issued.

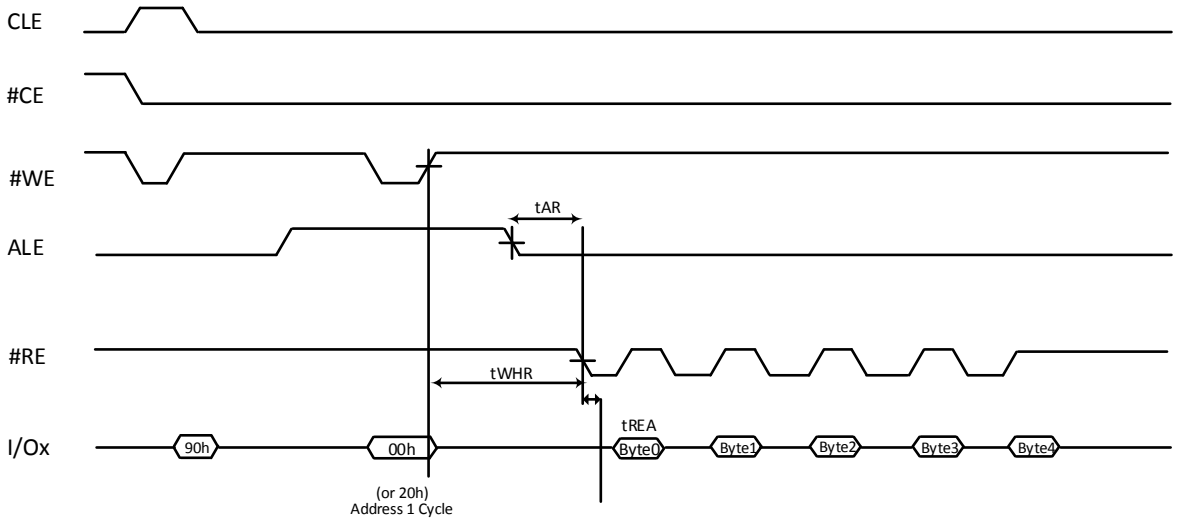

Figure 9-8 Read ID